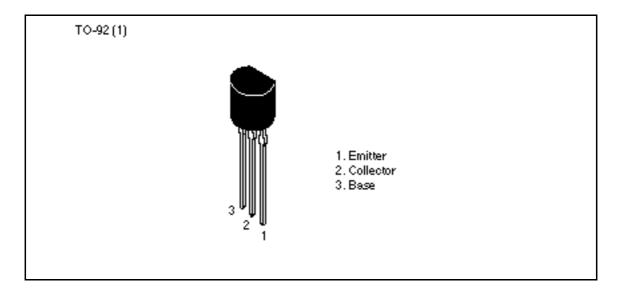
Silicon NPN Epitaxial

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Application

- Low frequency low noise amplifier
- Complementary pair with 2SA1190 and 2SA1191

Outline





Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol	2SC2855	2SC2856	Unit
Collector to base voltage	V_{CBO}	90	120	V
Collector to emitter voltage	V_{CEO}	90	120	V
Emitter to base voltage	V_{EBO}	5	5	V
Collector current	I _c	100	100	mA
Emitter current	I _E	-100	-100	mA
Collector power dissipation	P _c	400	400	mW
Junction temperature	Tj	150	150	°C
Storage temperature	Tstg	-55 to +150	-55 to +150	°C

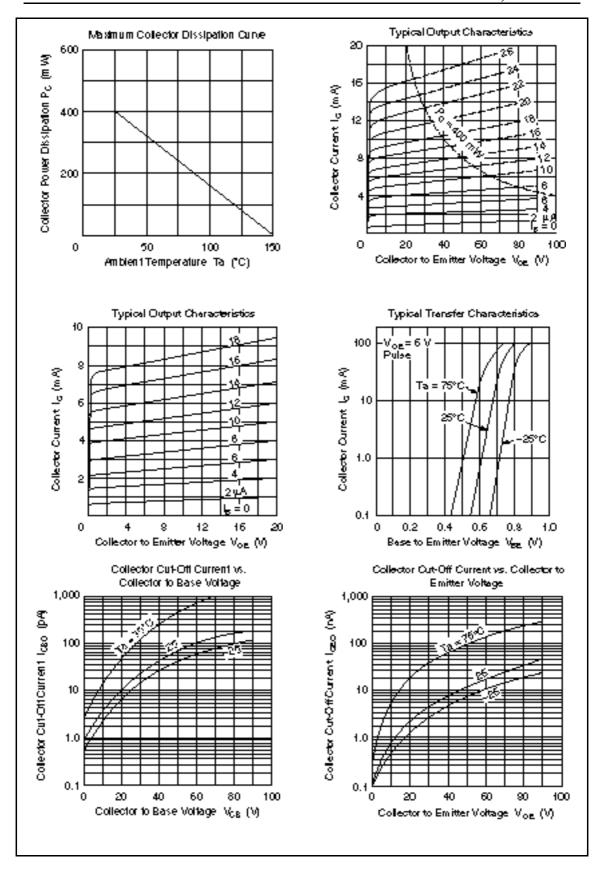
Electrical Characteristics ($Ta = 25^{\circ}C$)

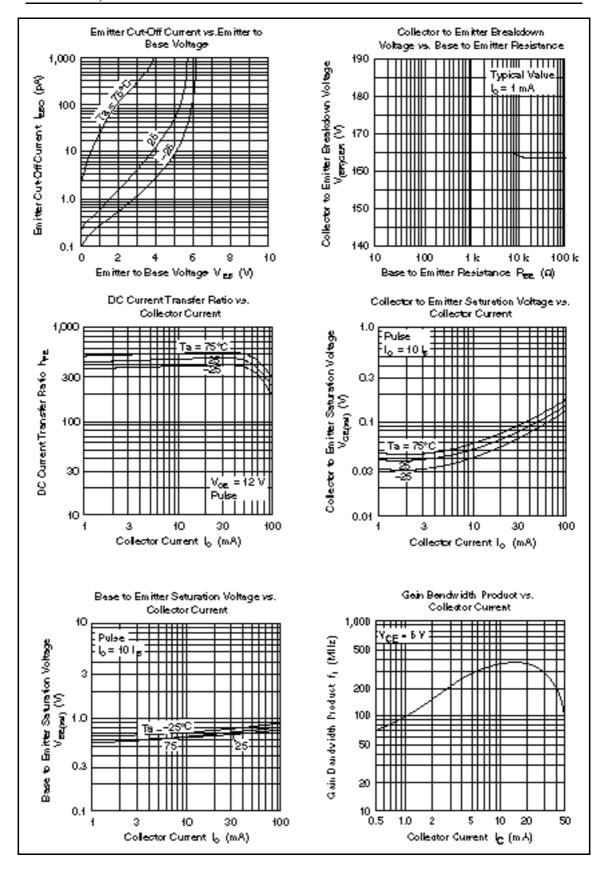
		2SC2855		2SC2856					
Item	Symbol	Min	Тур	Max	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	90	_	_	120	_	_	V	$I_{\rm C} = 10 \ \mu {\rm A}, \ I_{\rm E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	90	_	_	120	_	_	V	$I_{C} = 1 \text{ mA}, R_{BE} =$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	_	_	5	_	_	V	$I_{E} = 10 \mu A, I_{C} = 0$
Collector cutoff current	I _{CBO}	_	_	0.1	_	_	0.1	μΑ	$V_{CB} = 70 \text{ V}, I_{E} = 0$
Emitter cutoff current	I _{EBO}	_	_	0.1	_	_	0.1	μA	$V_{EB} = 2 \text{ V}, I_{C} = 0$
DC current transfer ratio	h _{FE} *1	250	_	800	250	_	800		$V_{CE} = 12 \text{ V}, I_{C} = 2 \text{ mA}^{*2}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	0.05	0.10	_	0.05	0.10	V	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 1 \text{ mA}^{*2}$
Base to emitter saturation voltage	$V_{\text{BE(sat)}}$	_	0.7	1.0	_	0.7	1.0	V	
Gain bandwidth product	f _T	_	310	_	_	310	_	MHz	$V_{CE} = 6 \text{ V}, I_{C} = 10 \text{ mA}$
Collector output capacitance	Cob	_	3	_	_	3	_	pF	$V_{CB} = 10 \text{ V}, I_{E} = 0,$ f = 1 MHz
Noise figure	NF	_	0.15	1.5	_	0.15	1.5	dB	$V_{CE} = 6 \text{ V}, I_{C} = 0.1 \text{ mA},$ $R_{g} = 10 \text{ k}, f = 1 \text{ kHz}$
		_	0.2	2.0	_	0.2	2.0	dB	$V_{CE} = 6 \text{ V}, I_{C} = 0.1 \text{ mA},$ $R_{g} = 10 \text{ k}, f = 10 \text{ Hz}$
Noise voltage referred to input	e _n	_	0.7	_	_	0.7	_	nV/ Hz	$V_{CE} = 6 \text{ V}, I_{C} = 10 \text{ mA},$ $R_{g} = 0, f = 1 \text{ kHz}$

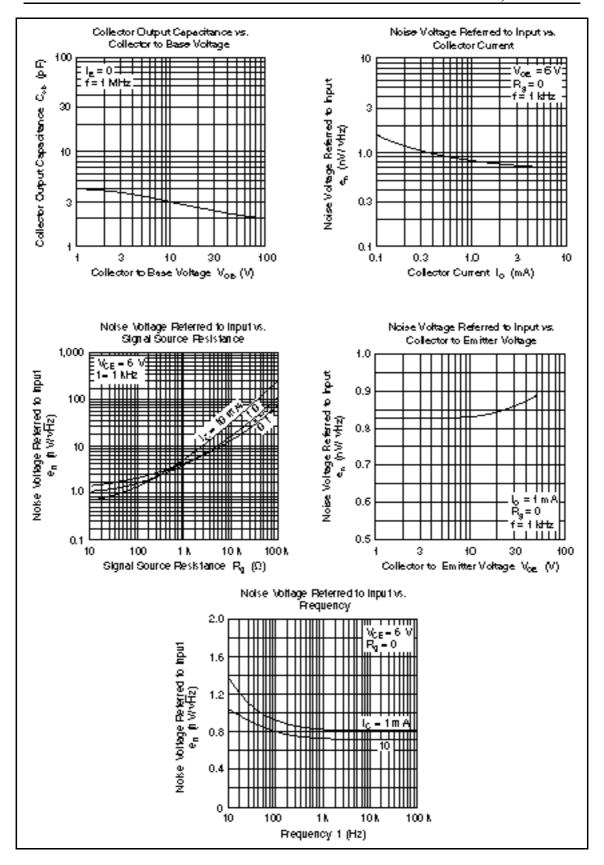
Notes: 1. The 2SC2855 and 2SC2856 are grouped by h_{FE} as follows.

2. Pulse test

D E 250 to 500 400 to 800







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